

Overview of the ATLAS Insertable B-Layer (IBL) Project

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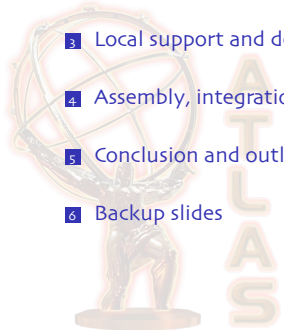
ATLAS

¹University of Oslo

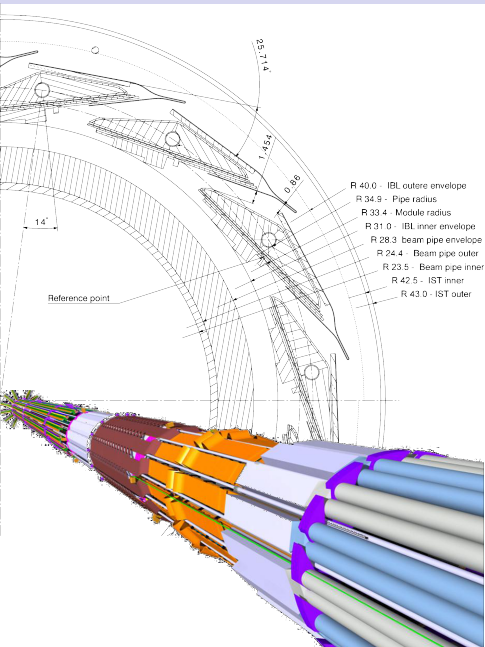
PIXEL2012 — 2012-09-03



- 1 Experimental background and detector layout
- 2 Electronics, sensors, and modules
- 3 Local support and detector services
- 4 Assembly, integration and installation
- 5 Conclusion and outlook
- 6 Backup slides



The ATLAS Insertable B-layer



Another ATLAS B-layer

Key parameters

- layout: 14 staves (turbine topology)
- module radius: R33.4 mm
- active length: 64 cm
- channels: 12 M pixels
- envelope: 9 mm cylindrical shell

To be installed during the long LHC shutdown (2013-14)

Insertable detector system

The active staves will be fitted with service extensions and integrated on the new R23.5 mm beam pipe. The 7 m long IBL package will be inserted through the aperture of the existing Pixel system.

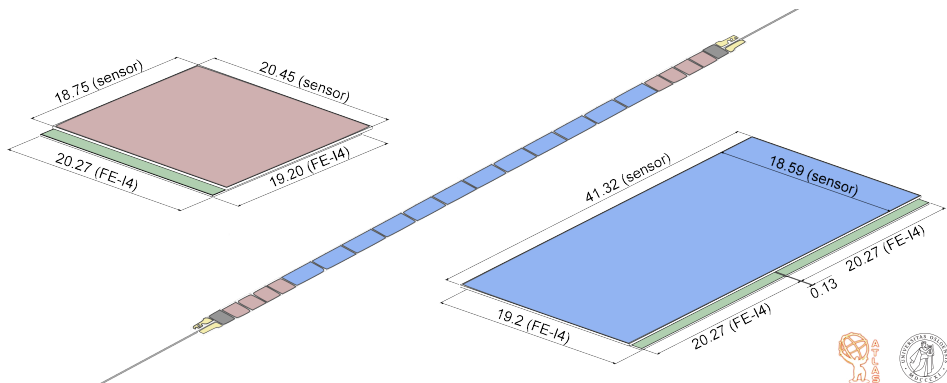
Detector modules on local support

25% single-chip modules:

- Double-sided 3D sensors
- Single front-end ASIC per module
- Four modules in one HV/LV service group
- Deployed at the high- η ends of the staves

75% double-chip modules:

- Slim-edge n+-in-n planar sensors
- Two front-end ASICs per module
- Two modules in one HV/LV service group
- Covers the central part of the detector



Frontend electronics: the FE-I4 135 nm CMOS ASIC

Requirements:

Pixel size: $50 \times 250 \mu\text{m}^2$

Organization: 336×80 (rows \times cols)

Threshold: $4000 e^-$ (in-time)

Dispersion: $100 e^-$ (tuned)

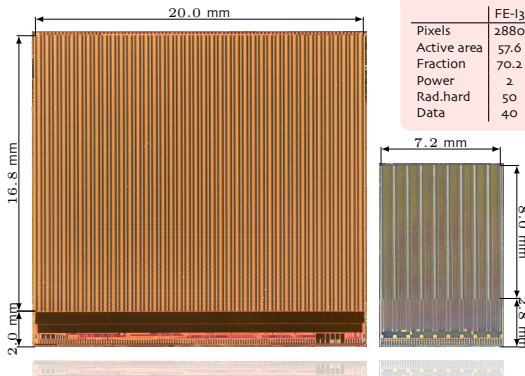
Noise: $< 300 e^-$
(400 FF)

Pixel capacitance: $0 - 500 \text{ fF}$

Charge resolution: 4 bits (TOT)

Comparison:

	FE-I3	FE-I4	
Pixels	2880	26880	
Active area	57.6	336	mm^2
Fraction	70.2	88.5	%
Power	2	2	mW/mm^2
Rad.hard	50	250	MRad
Data	40	160	Mbs

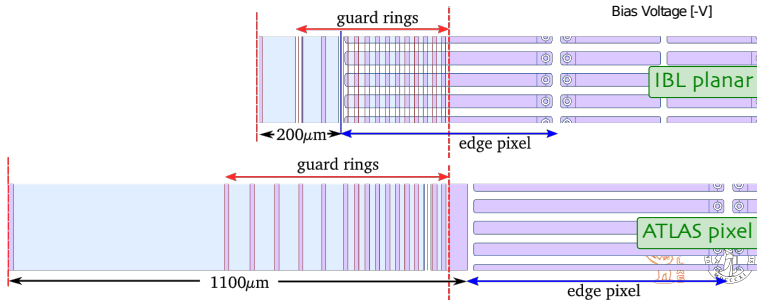
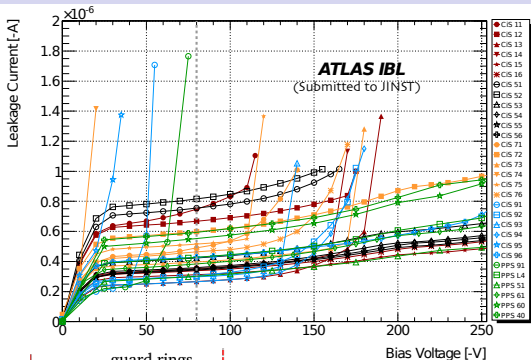


FE-I4 - features and innovations:

- Four-Pixel Digital Readout (4PDR) hit processing unit
- Distributed memory trigger latency buffering
- Single-chip module stand-alone operation
- Built-in low drop-out (LDO) regulators and references
- High-speed 8bit/10bit encoded data output

Slim-edge n⁺-in-n planar sensors

- Slim-edge design, guard rings overlap opposing edge-pixels
- Processed on 200 μm oxygenated high-resistivity FZ wafers
- Fabrication with CiS (Germany)
- Single-chip sensors for prototype tests
- Double-chip sensors for production modules
- Production yield: $\approx 90\%$ (includes UBM/dicing)



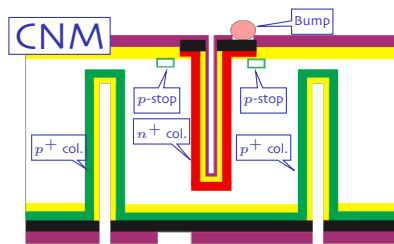
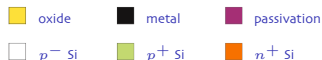
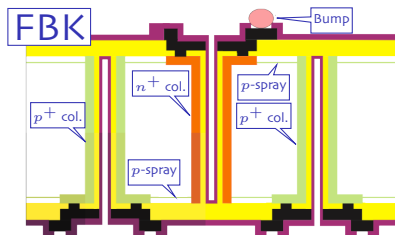
Double-sided double-type columns 3D sensors

The 3D-sensors have been developed in cooperation with two vendors:

FBK: Fondazione Bruno Kessler (Trento, Italy)

CNM: Centro Nacional de Microelectronica (Barcelona, Spain)

There are small variations in the processes, both vendors fabricate their sensors on identical 4" FZ p-type high resistivity wafers



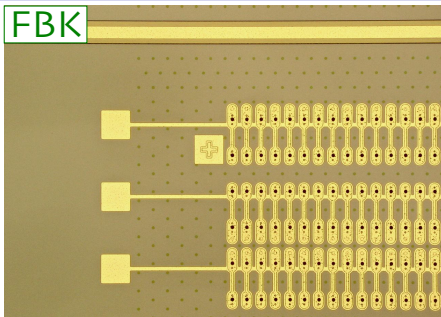
FBK Process:

- *p*-spray insulation, both sides
- Full-depth electrodes
- Unfilled columns

CNM Process:

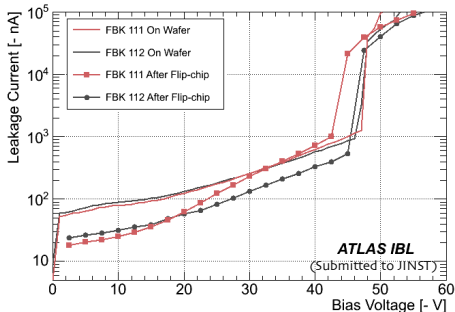
- Top-side *p*-stop insulation
- Electrodes don't reach full depth
- Partially filled columns

FBK edge design



Edge design

At the edge are *guard fence posts*; rows of ohmic columns that protects the depleted bulk from edge effects.



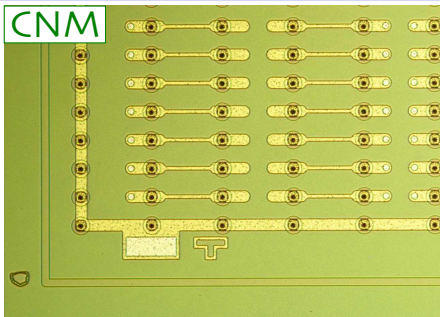
Triage and acceptance

Wafer-level IV measurements important for selecting good sensor tiles for hybridization:

- Temporary metal layer shorts columns of read-out electrodes
- Full bulk current available summing across 80 columns

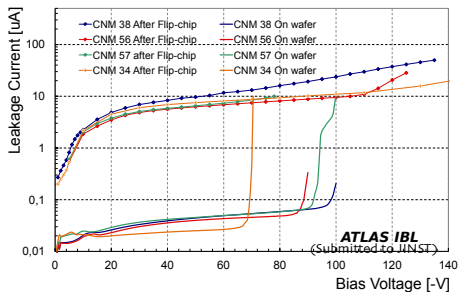
Method correlates well with final module IV measurements.

CNM edge design



Edge design

The sensor bulk is protected from edge effects by a $n+$ 3D guard ring at ground potential and opposing ohmic columns at bias voltage.



Triage and acceptance

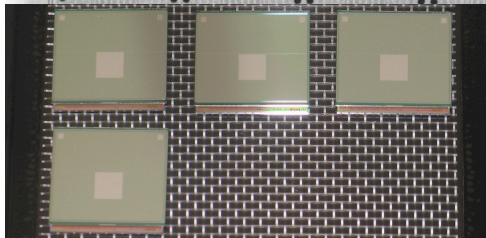
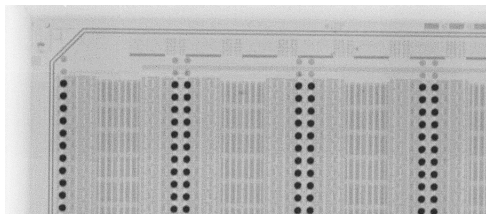
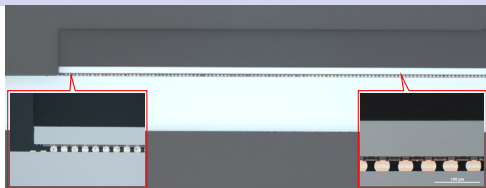
No temp. metal, wafer-level IV measurements considers only the leakage current collected by the guard ring, which turns out to be sufficiently correlated with bulk IV measurements on hybrid modules

Detector module hybridization with IZM (Germany)

Bump-bonding of very large, thinned FE chips:

- FE-I4 wafer thinned to 150 μm
- Attached to glass support wafer
- Fine-pitch SnAg micro-bump deposition
- Sensor wafer electroplating under-bump metalization (UBM)
- Dicing and flip-chip soldering
- Back-side laser removal of glass support
- X-ray and optical inspection

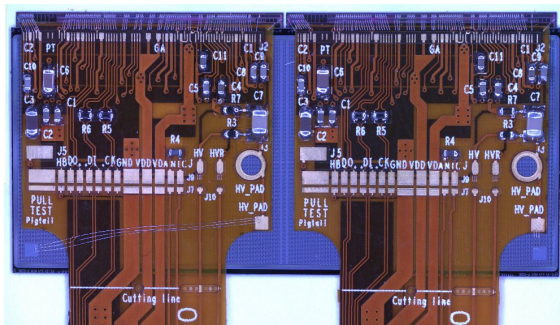
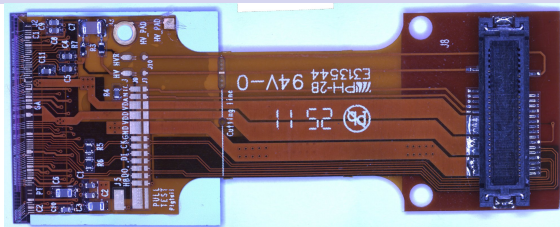
Thinning to 100 μm results in some ASIC breakage during laser removal; 150 μm thickness is a conservative yield/material compromise.



Testable modules, *dressed* with the module flex

Module flex carries discrete passives; notably the low-profile HV capacitor and LVDS termination resistors.

The FE-I4 signal and power lines are temporarily wire bonded to the disposable pigtail, allowing full read-out testing during QA. The USBPix PC-based read-out system is designed for this purpose. As the module is prepared for loading on stave the pigtail is cut and the bridging wire-bonds are removed.



Projected radiation load

Toward end-of-service (550 fb^{-1}) the IBL radiation load is expected to reach:

NIEL: $6 \times 10^{15} \text{ n/cm}^2$ (1 MeV n eq.)

TID: 250 MRad

FE-I4 total ionizing dose (TID)

Tested to 200 MRad at the Los Alamos Laboratory (800 MeV protons); minimal change to threshold dispersion and 15 – 25% increase in noise.

Incidentally exposed to 750 MRad during module irradiation at KIT; dead/noisy pixels mostly recovered by FE reconfiguration

Single event upset (SEU)

Tests performed at CERN PS (24 GeV protons). **DICE** hardened registers have SEU cross-sections of order $1 \times 10^{-15} \text{ cm}^2$.

Module irradiation

Detector modules are irradiated up to $5 \times 10^{15} \text{ n/cm}^2$:

KIT: 25 MeV protons (Karlsruhe, Germany)

TRIGA: fast reactor neutrons (Ljubljana, Slovenia).

Following irradiation modules were annealed 60 C/2 h then stored cold



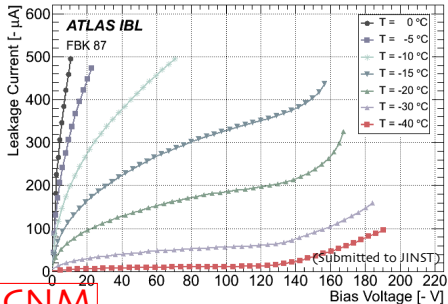
IV-measurements after irradiation

FBK

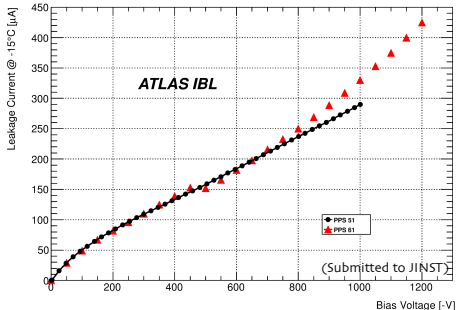
Dominantly ohmic behavior; as expected after irradiation.

CiS: Well within sensor power dissipation limits (200 mW/cm² thermal runaway safety)

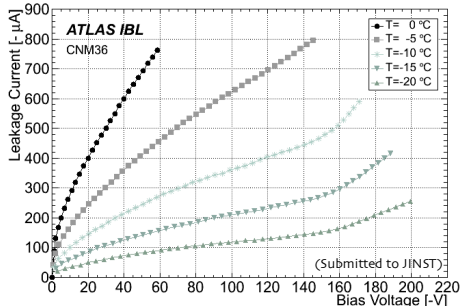
FBK/CNM: No signs of breakdown or thermal runaway.



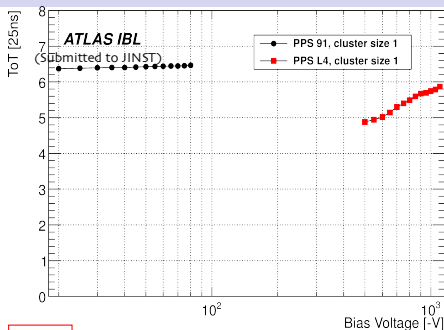
CiS



CNM

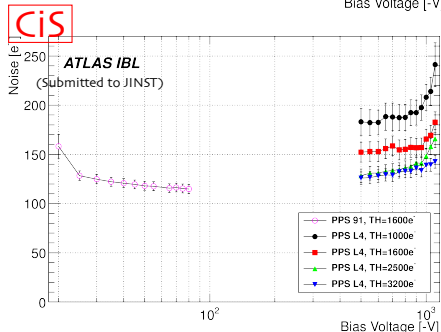


Planar sensors: signal and noise before/after irradiation

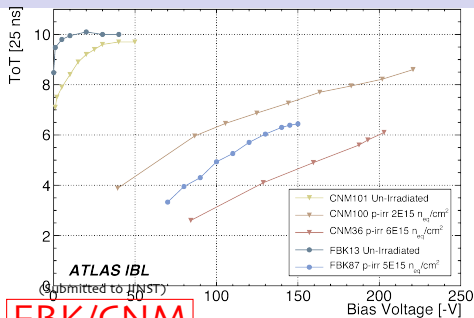


Note: pre/post irradiation are different samples

- Signal is most probable value (MPV) of ⁹⁰Sr
- Charge in uncalibrated units of time-over-threshold (ToT)
- Indications of charge multiplication toward 1 kV
- Noise is well under control also after irradiation

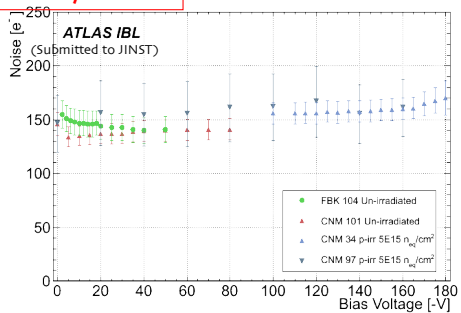


3D sensors: signal and noise before/after irradiation



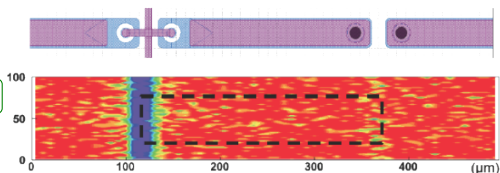
FBK/CNM

- Note: pre/post irradiation are different samples
- Regulated cooling to fix sensor temperature at -15 C
 - Signal is most probable value (MPV) of ^{90}Sr quasi-MIPs (1-pixel hits).
 - Charge in uncalibrated units of time-over-threshold (ToT)
 - Satisfactory signal efficiency at/above 160 V
 - Noise sensitive to thresholds, but well under control for realistic operating points

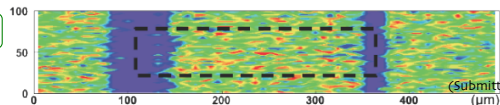


Irradiated sensor efficiency maps

PPS 61 (15° , -1000 V): 96.9%

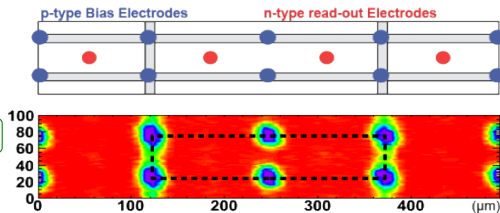


PPS 61 (15° , -600 V): 86.4%

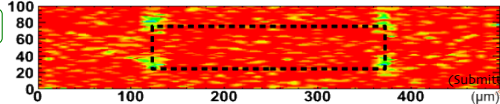


(Submitted to JINST)

CNM 81 (0° , -160 V): 97.5%

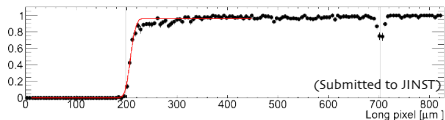


CNM 34 (15° , -160 V): 99.0%

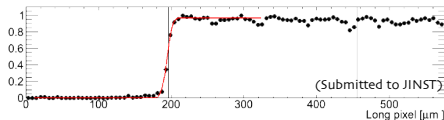


(Submitted to JINST)

Irradiated sensor edge efficiency



CNM 34: $V_b = -140 \text{ V}$

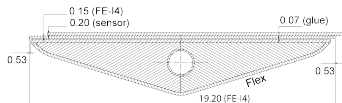
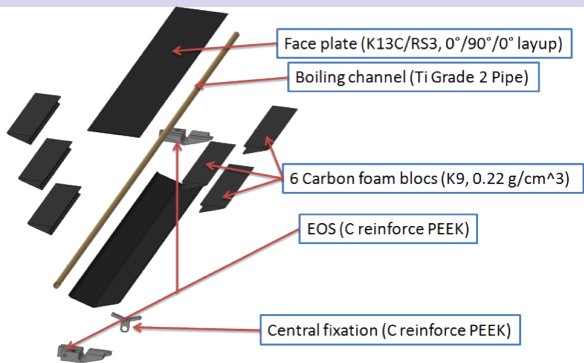


PPS L2: $V_b = -1000 \text{ V}$

Both planar and 3D sensors reach 50% efficiency approximately 200 μm from the physical dicing edge.



Local support, electrical services



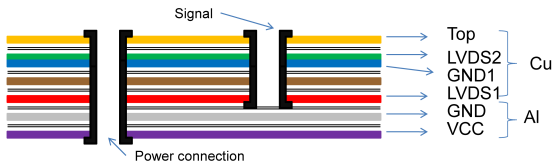
Bare stave

Skinned, low density carbon foam construction - embedded 1.5 mm Ti boiling channel.

Pressure: 150 bar (max test)

TFoM: < 15 Kcm²/W

X/X₀: 0.6%



Flex bus

Runs along back of stave, lateral wings fold around the edge to connect to modules

Cooling system

Requirements:

The two most demanding operational requirements come from **beampipe bake-out** and safety against **thermal runaway** for deeply radiation-damaged sensors.

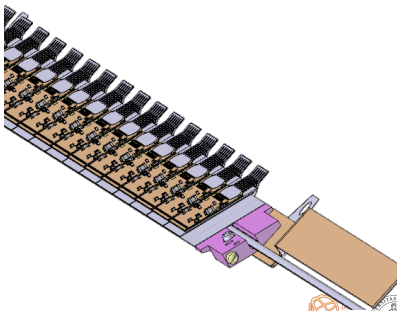
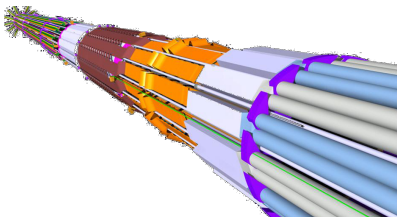
Max. power	1.5 kW
Max. test pressure	150 bar
Range of operation	-40 C . . . + 20 C
Thermal stability	< 0.5 C

2PACL - two-phase accumulator-controlled loop

The IBL cooling is a CO₂-based evaporative system, essentially derived from the LHCb/Velo-system. Benefits of 2PACL-operation:

- No compressor inside the active detector loop
- No back-pressure regulators
- No exhaust vapor heaters
- Accumulator volume provides regulation inertia

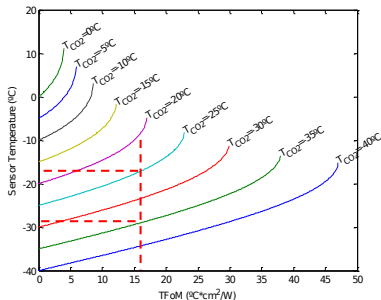
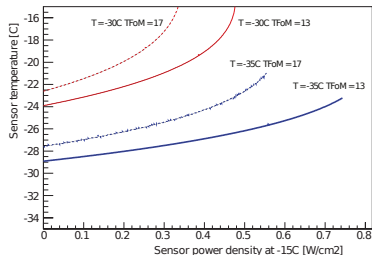
The small-diameter pipes and corresponding volume contributes to minimizing the material budget.



Cooling simulations - thermal runaway safety

Detector operation at end-of-life (planar sensors)

Accumulated fluence	$5 \times 10^{15} \text{ n}_{\text{eq}}/\text{cm}^2$	(safety factors)
Chip power density	$290 \text{ mW}/\text{cm}^2$	
Sensor bias voltage	1000 V	
Sensor power density	$80 \text{ mW}/\text{cm}^2$	(annealed)
at $T_0 = -15 \text{ C}$	$160 \text{ mW}/\text{cm}^2$	(not annealed)
	$200 \text{ mW}/\text{cm}^2$	(design max.)



Self-coupling runaway model:

Leakage current scaling law:

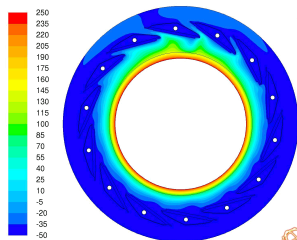
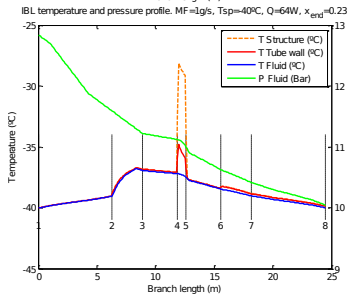
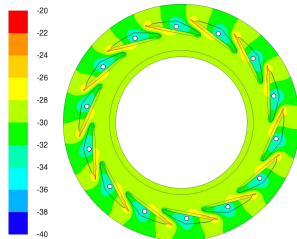
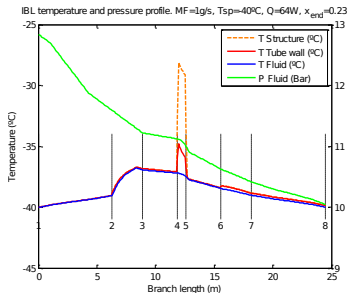
$$I = I_0 \left(\frac{T}{T_0} \right)^2 \exp \left(\frac{E_g}{2 k_B} \left(\frac{1}{T_0} - \frac{1}{T} \right) \right)$$

Linear heat-conduction model:

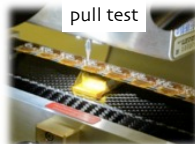
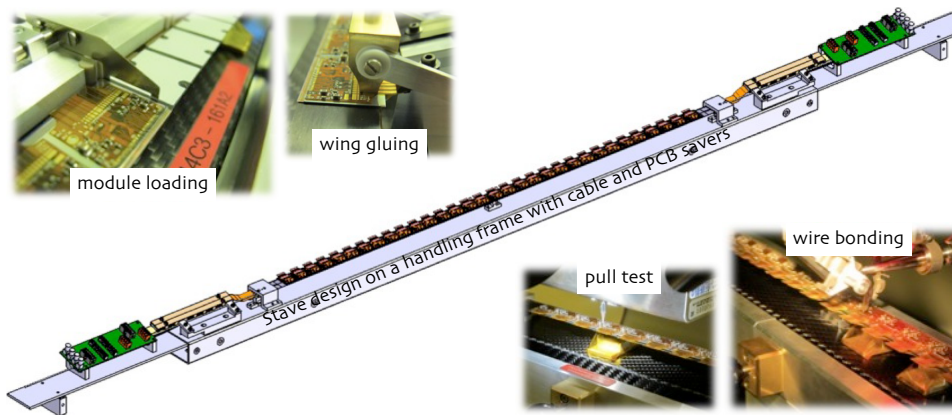
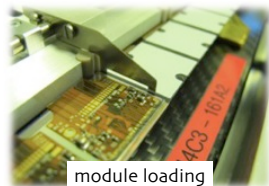
$$T = T_{\text{coolant}} + \frac{\Gamma}{A_{\text{sensor}}} (P_{\text{sensor}} + P_{\text{fe}})$$

Measured thermal figure of (dis-) merit: $\Gamma = 13 \text{ Kcm}^2/\text{W}$

Cooling simulations - nominal and beam-pipe bake-out



Stave assembly - tooling



Stave assembly completed, tests in progress



- ATLAS Insertable B-Layer Technical Design Report. CERN-LHCC-2010-013/ATLAS-TDR-019
- ATLAS Insertable B-Layer Technical Design Report Addendum. CERN-LHCC-2012-009/ATLAS-TDR-019-ADD-1
- Prototype ATLAS IBL Modules using the FE-I4A Front-End Readout Chip. Submitted to JINST (2012)



- The FE-14 ASIC is qualified and in delivery
- Slim-edge planar and 3D sensors are qualified and manufactured
- Module hybridization is in production
- Mechanics and services are qualified and in production
- Evaluation of pre-production staves is ongoing
- The final decision about the installation strategy is pending

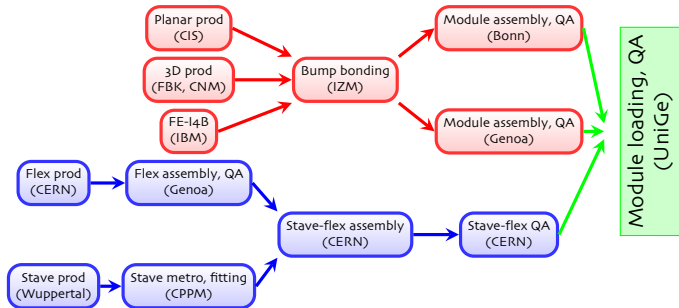




- Underground insertion into ATLAS
- On surface pre-integration with Pixels
- Final decision subject to the fate of the nSQP-project



Stave assembly - Production flow



Module loading (UniGe)

- Reception QA
- Load modules
- Wing gluing
- Wire bonding, QA
- *Thermal cycling (preseries)*
- Metrology, envelope QA
- Readout tests

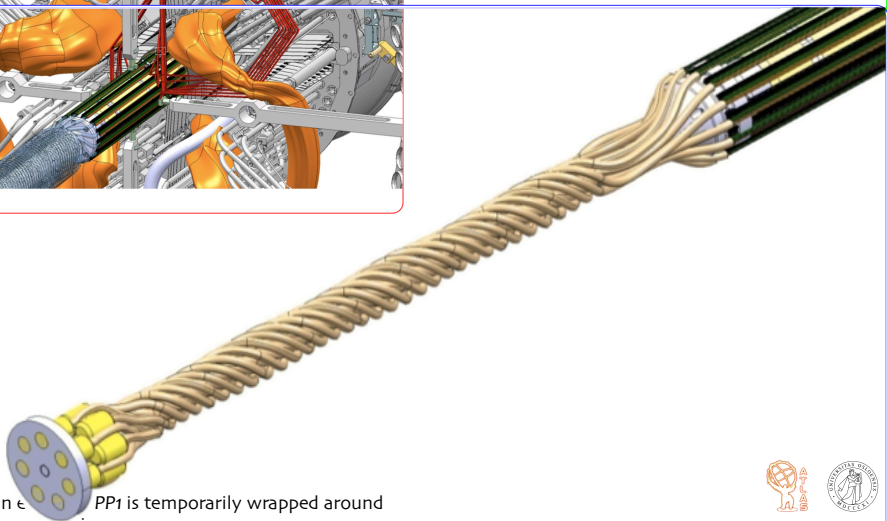
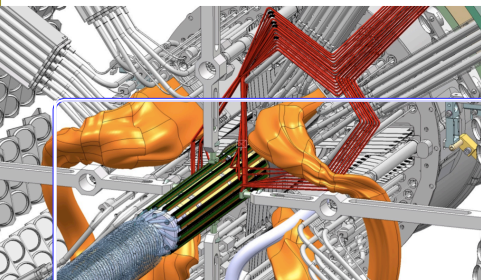
Staves integration (SR1)

- Stave burn-in, QA
- Braze pipe extension
- Integrate staves on beam pipe
- Final on-surface tests and pre-commissioning



Insertable package

All far-side Type-1 services must pass through IBL aperture during insertion



Length in ϵ PP1 is temporarily wrapped around beam-pipe extension

